Abstracts

SiGe bipolar technologies for low phase noise RF and microwave applications (2000 Vol. I [MWSYM])

M. Regis, M. Borgarino, L. Bary, O. Llopis, J. Graffeuil, A. Gruhle, S. Kovacic and R. Plana. "SiGe bipolar technologies for low phase noise RF and microwave applications (2000 Vol. I [MWSYM])." 2000 MTT-S International Microwave Symposium Digest 00.1 (2000 Vol. I [MWSYM]): 261-264.

This paper presents an overview of the low frequency noise performances of both "abrupt" and "gradual" SiGe HBTs. We demonstrated that when an appropriate device is used, a 1/f corner noise frequency of 1 kHz is obtained. We further presented a correlation with phase noise performances which outperform those reported for III-V devices.

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